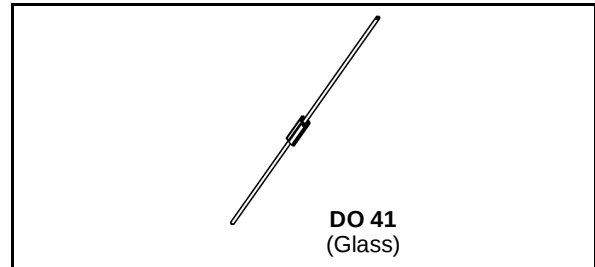


**SMALL SIGNAL SCHOTTKY DIODE****DESCRIPTION**

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching. This device has integrated protection against excessive voltage such as electrostatic discharges.

**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		80	V
I_F	Forward Continuous Current*	$T_a = 70^\circ\text{C}$	500	mA
I_{FRM}	Repetitive Peak Forward Current*	$t_p = 1\text{s}$ $\delta \leq 0.5$	3	A
I_{FSM}	Surge non Repetitive Forward Current*	$t_p \leq 10\text{ms}$	10	A
T_{stg} T_j	Storage and Junction Temperature Range		- 65 to 150 - 65 to 125	$^\circ\text{C}$ $^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering during 10s at 4mm from Case		230	$^\circ\text{C}$

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	110	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS**STATIC CHARACTERISTICS**

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I_R^{**}	$T_j = 25^\circ\text{C}$	$V_R = 80\text{V}$			200	μA
V_F^{**}	$T_j = 25^\circ\text{C}$	$I_F = 10\text{mA}$			0.32	V
	$T_j = 25^\circ\text{C}$	$I_F = 100\text{mA}$			0.42	
	$T_j = 25^\circ\text{C}$	$I_F = 1\text{A}$			1	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	$T_j = 25^\circ\text{C}$	$f = 1\text{MHz}$		120		pF
		$V_R = 5\text{V}$		35		

* On infinite heatsink with 4mm lead length

** Pulse test: $t_p \leq 300\mu\text{s}$ $\delta < 2\%$.